

HTZ250G Series

$$I_{F(AV)} = 2.7 \text{ A}$$

$$V_{RRM} = 44800 \text{ V}$$

High Voltage Diode Rectifier Module

LARONTROL
Electronic Devices

Type Number	Repetitive Peak	Minimum Avalanche Voltage $V_{(BR)R}$	
HTZ250G44K	44800	47600	
HTZ250G39K	39200	42000	
HTZ250G33K	33600	36400	
HTZ250G28K	28000	30800	

CIRCUIT DIAGRAM



CURRENT RATINGS - AIR COOLED

$I_{F(AV)}$	Mean forward current
I_F	Continuous (direct) forward current
$R_{th(j-a)}$	Thermal resistance junction to ambient

Half wave resistive load $T_{amb} = 35^\circ\text{C}$

2.7	A
3.3	A
1.8	$^\circ\text{C/W}$

CURRENT RATINGS - OIL COOLED

$I_{F(AV)}$	Mean forward current
I_T	Continuous (direct) forward current
$R_{th(j-o)}$	Thermal resistance junction to oil

Half wave resistive load $T_{oil} = 60^\circ\text{C}$

3.5	A
4.3	A
0.97	$^\circ\text{C/W}$

SURGE RATINGS

I^2t	I^2t for fusing
I_{FSM}	Surge (non-repetitive) forward current

10 ms half sine $T_{vj} = 150^\circ\text{C}$

200	A^2sec
200	A

TEMPERATURE AND FREQUENCY RATINGS

T_{vj}	Virtual junction temperature
T_{stg}	Storage temperature range
f	Frequency range

Forward (conducting)
Reverse (blocking)

180	$^\circ\text{C}$
180	$^\circ\text{C}$
-40 to 100	$^\circ\text{C}$
20 to 400	Hz

CHARACTERISTICS $T_{case} = 25^\circ\text{C}$ unless otherwise stated

V_{FM}	Forward voltage
I_{RM}	Peak reverse current

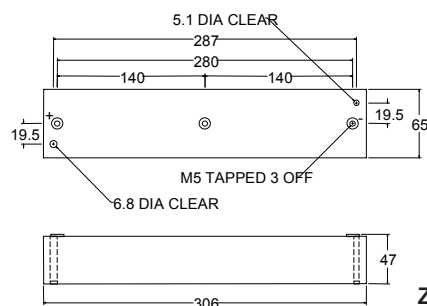
At 12 Amps peak
At V_{RRM} , $T_{case} = 150^\circ\text{C}$

max 32	V
max 0.5	mA

Dimensioned Outlines

Dimensions shown are maximum in mm

Weight typ.: 2,0 Kg



IXYS reserves the right to change limits, test conditions and dimensions.

ZG

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